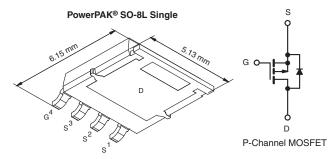


www.vishay.com

Vishay Siliconix

Automotive P-Channel 200 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY	
V _{DS} (V)	- 200
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.213
$R_{DS(on)}(\Omega)$ at $V_{GS} = -6 \text{ V}$	0.221
I _D (A)	- 12
Configuration	Single



FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- AEC-Q101 Qualifiedd
- 100 % R_q and UIS Tested
- Compliant to RoHS Directive 2002/95/EC





COMPLIANT HALOGEN FREE

ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and Halogen-free	SQJ431EP-T1-GE3

ABSOLUTE MAXIMUM RATINGS	(T _C = 25 °C, unles	s otherwise noted)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	- 200	V
Gate-Source Voltage		V _{GS}	± 20	V
Continuous Drain Current	T _C = 25 °C	1	- 12	
Continuous Drain Current	T _C = 125 °C	l _D	- 7	
Continuous Source Current (Diode Conduction) ^a		I _S	- 30	Α
Pulsed Drain Current ^b		I _{DM}	- 40	
Single Pulse Avalanche Current	l 0.1 mll	I _{AS}	- 40	
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	80	mJ
Maximum Power Dissipation ^b	T _C = 25 °C	PD	83	W
Maximum Power Dissipation	T _C = 125 °C	VV		
Operating Junction and Storage Temperature	Range	T _J , T _{stg}	- 55 to + 175	°C
Soldering Recommendations (Peak Temperate	ure) ^{e, f}		260	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^c	R_{thJA}	65	°C/W
Junction-to-Case (Drain)		R_{thJC}	1.8	C/VV

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.
- e. See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8L. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- f. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static					•		
Drain-Source Breakdown Voltage	V_{DS}	V _{GS}	= 0, I _D = - 250 μA	- 200	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	V_{GS} , $I_{D} = -250 \mu A$	- 2.5	- 3.0	- 3.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = - 200 V	-	-	- 1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = - 200 V, T _J = 125 °C	-	-	- 50	μA
		$V_{GS} = 0 V$	V _{DS} = - 200 V, T _J = 175 °C	-	-	- 150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = - 10 V	V _{DS} ≤ - 5 V	- 16	-	-	Α
		V _{GS} = - 10 V	I _D = - 3.8 A	-	0.178	0.213	
Drain-Source On-State Resistance ^a	D	V _{GS} = - 10 V	I _D = - 3.8 A, T _J = 125 °C	-	-	0.409	Ω
Dialii-Source Oil-State nesistance	R _{DS(on)}	V _{GS} = - 10 V	I _D = - 3.8 A, T _J = 175 °C	-	-	0.527	52
		V _{GS} = - 6 V	I _D = - 3.8 A	-	0.182	0.221	
Forward Transconductanceb	9 _{fs}	V _{DS} =	- 15 V, I _D = - 3.8 A	-	16	-	S
Dynamic ^b							
Input Capacitance	C _{iss}			-	3483	4355	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = - 25 V, f = 1 MHz	-	193	245	pF
Reverse Transfer Capacitance	C _{rss}			-	125	160	
Total Gate Charge ^c	Qg			-	71	106	
Gate-Source Charge ^c	Q_{gs}	V _{GS} = - 10 V	$V_{DS} = -100 \text{ V}, I_{D} = -5.2 \text{ A}$	-	13.8	-	nC
Gate-Drain Charge ^c	Q_{gd}			-	21.6	-	
Gate Resistance	R_{g}		f = 1 MHz	1.2	2.4	3.6	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	15	23	
Rise Time ^c	t _r	V _{DD} = -	100 V, R_L = 20.8 Ω	-	11	17	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong -4.8 \text{ A},$	$V_{GEN} = -10 \text{ V}, R_g = 1.0 \Omega$	-	44	66	ns
Fall Time ^c	t _f	7		-	10	15	
Source-Drain Diode Ratings and Chara	acteristics ^b	•			•		
Pulsed Current ^a	I _{SM}			-	-	- 40	Α
Forward Voltage	V_{SD}	I _F = -5 A, V _{GS} = 0 0.8 - 1.		- 1.2	V		

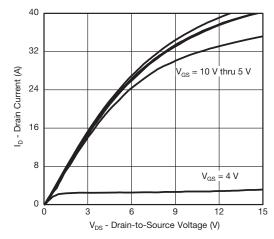
Notes

- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

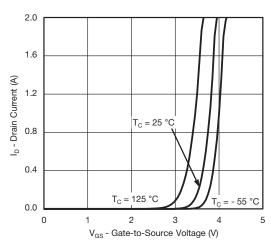
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



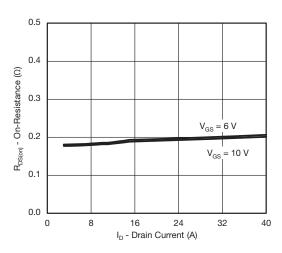
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



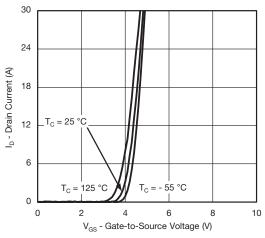
Output Characteristics



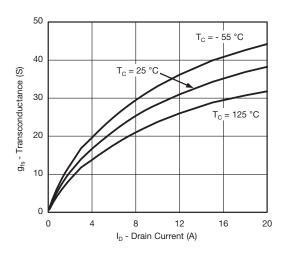
Transfer Characteristics



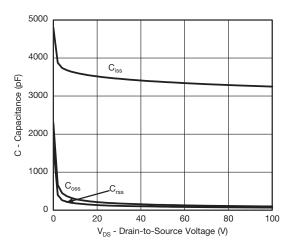
On-Resistance vs. Drain Current



Transfer Characteristics



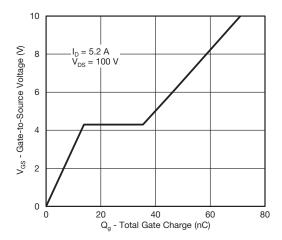
Transconductance



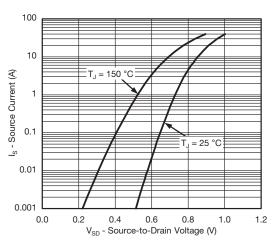
Capacitance



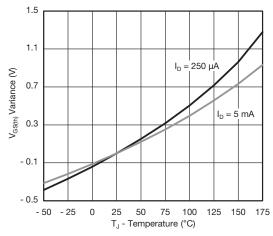
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



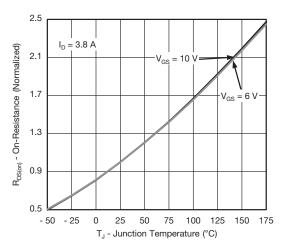
Gate Charge



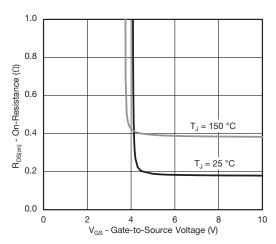
Source Drain Diode Forward Voltage



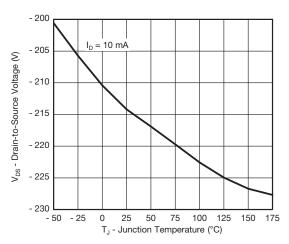
Threshold Voltage



On-Resistance vs. Junction Temperature

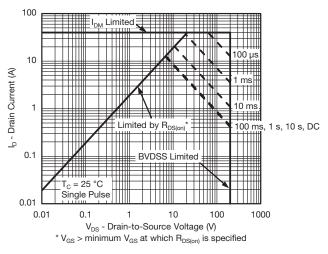


On-Resistance vs. Gate-to-Source Voltage

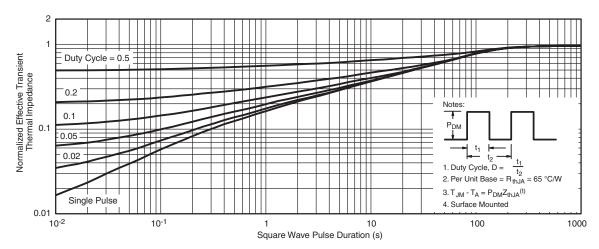


Drain Source Breakdown vs. Junction Temperature

THERMAL RATINGS ($T_C = 25$ °C, unless otherwise noted)



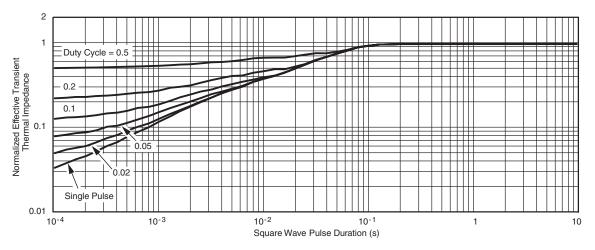
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_C = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

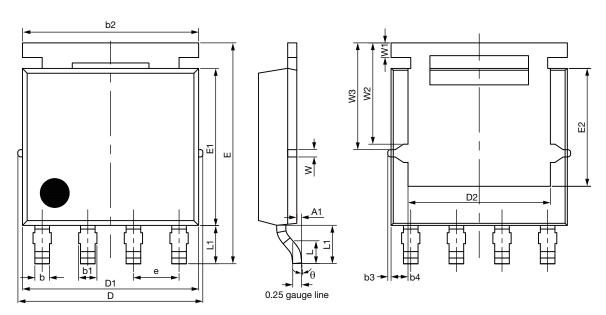
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?67033.

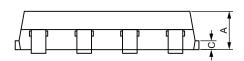
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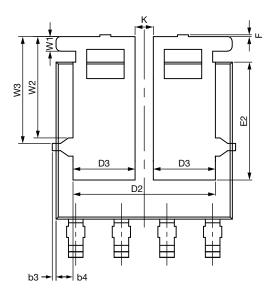
PowerPAK® SO-8L Case Outline for Non-Al Parts





Backside view (single)





Backside view (dual)

Revision: 16-May-16 1 Document Number: 69003



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DIM	MILLIMETERS			INCHES		
DIM.	MIN.	NOM.	MAX.	MIN. NOM.		MAX
Α	1.00	1.07	1.14	0.039	0.042	0.045
A1	0.00	-	0.127	0.00	-	0.005
b	0.33	0.41	0.48	0.013	0.016	0.019
b1	0.44	0.51	0.58	0.017	0.020	0.023
b2	4.80	4.90	5.00	0.189	0.193	0.197
b3		0.094			0.004	
b4		0.47			0.019	
С	0.20	0.25	0.30	0.008	0.010	0.012
D	5.00	5.13	5.25	0.197	0.202	0.207
D1	4.80	4.90	5.00	0.189	0.193	0.197
D2	3.86	3.96	4.06	0.152	0.156	0.160
D3	1.63	1.73	1.83	0.064	0.068	0.072
е		1.27 BSC		0.050 BSC		
E	6.05	6.15	6.25	0.238	0.242	0.246
E1	4.27	4.37	4.47	0.168	0.172	0.176
E2	3.18	3.28	3.38	0.125	0.129	0.133
F	-	-	0.15	-	-	0.006
L	0.62	0.72	0.82	0.024	0.028	0.032
L1	0.92	1.07	1.22	0.036	0.042	0.048
K		0.51			0.020	
W	0.23				0.009	
W1	0.41			0.016		
W2		2.82		0.111		
W3		2.96			0.117	
θ	0°	-	10°	0°	-	10°

ECN: T16-0221-Rev. D, 16-May-16

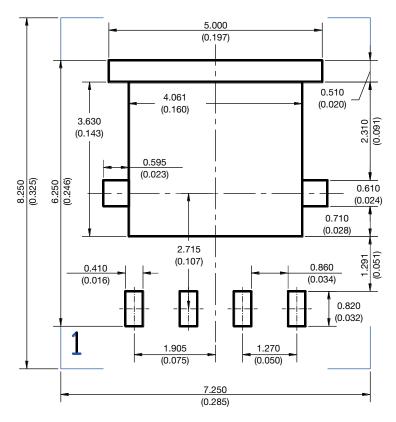
DWG: 5976

Note

• Millimeters will gover



RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)



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